

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
100V	1.85mΩ @ V _{GS} = 10V	250A

Description and Applications

This new generation N-Channel enhancement mode MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

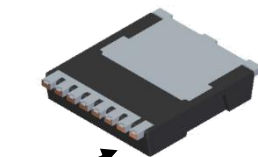
Applications

- Motor controls
- DC-DC converters
- Power managements

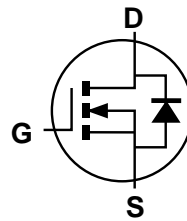
POWERDI1012-8



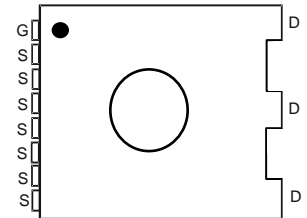
Top View



Bottom View



Internal Schematic



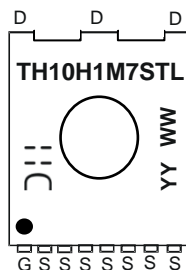
Top View
Pin Configuration

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMTH10H1M7STLW-13	POWERDI1012-8	1,500	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



PowerDI1012-8

J = Manufacturer's Marking
 TH10H1M7STL = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 25 = 2025)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	T _C = +25°C 250	A
		T _C = +100°C 176	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	1000	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	250	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	1000	A
Avalanche Current, L = 0.3mH	I _{AS}	73	A
Avalanche Energy, L = 0.3mH	E _{AS}	799.4	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	6	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	24	°C/W
Total Power Dissipation (Note 6)	P _D	T _C = +25°C 250	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	0.6
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 80V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.4	1.85	mΩ	V _{GS} = 10V, I _D = 30A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _S = 30A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	9871	—	pF	V _{DS} = 50V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	3019	—		
Reverse Transfer Capacitance	C _{rss}	—	58	—		
Gate Resistance	R _g	—	2.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	147	—	nC	V _{DD} = 50V, I _D = 30A, V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	43	—		
Gate-Drain Charge	Q _{gd}	—	32	—		
Turn-On Delay Time	t _{D(ON)}	—	29	—	ns	V _{DD} = 50V, V _{GS} = 10V, I _D = 30A, R _g = 4.7Ω
Turn-On Rise Time	t _r	—	64	—		
Turn-Off Delay Time	t _{D(OFF)}	—	108	—		
Turn-Off Fall Time	t _f	—	69	—		
Reverse-Recovery Time	t _{RR}	—	91	—	ns	I _F = 25A, di/dt = 100A/µs
Reverse-Recovery Charge	Q _{RR}	—	270	—	nC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

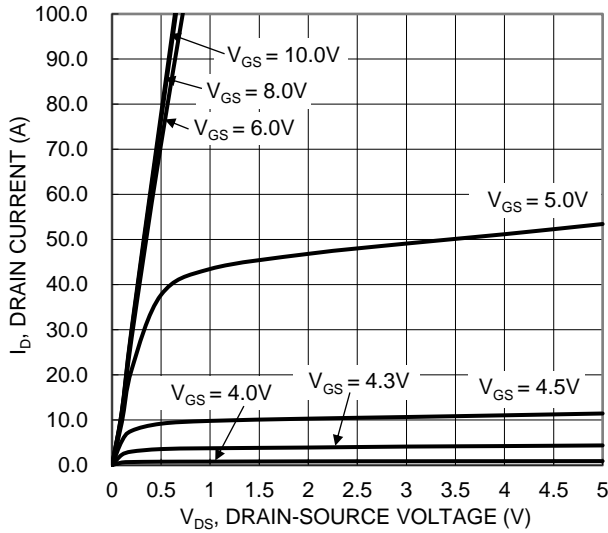


Figure 1. Typical Output Characteristic

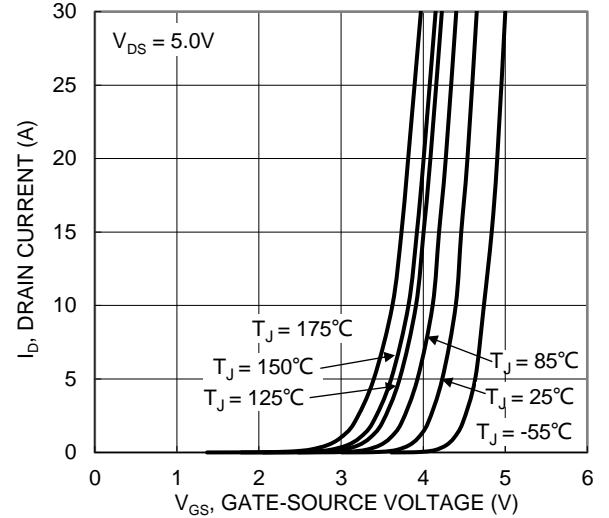


Figure 2. Typical Transfer Characteristic

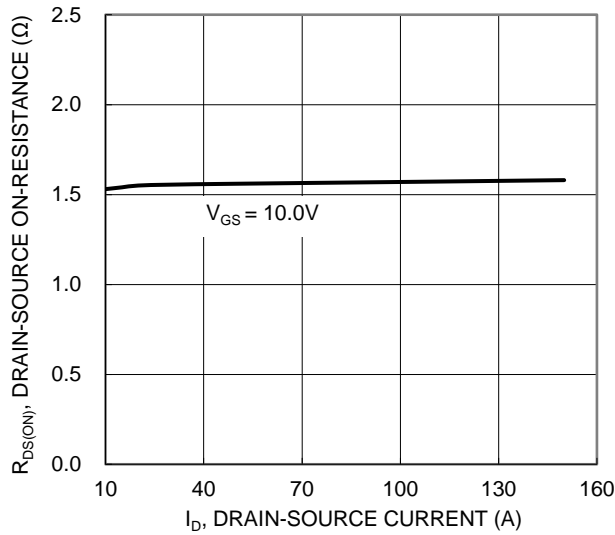


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

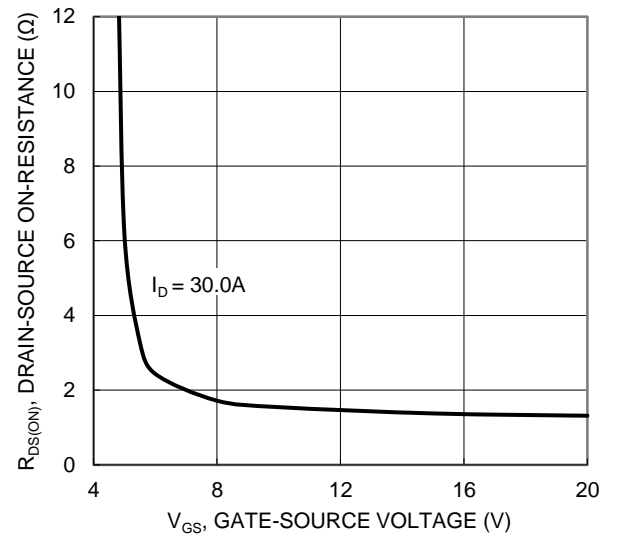


Figure 4. Typical Transfer Characteristic

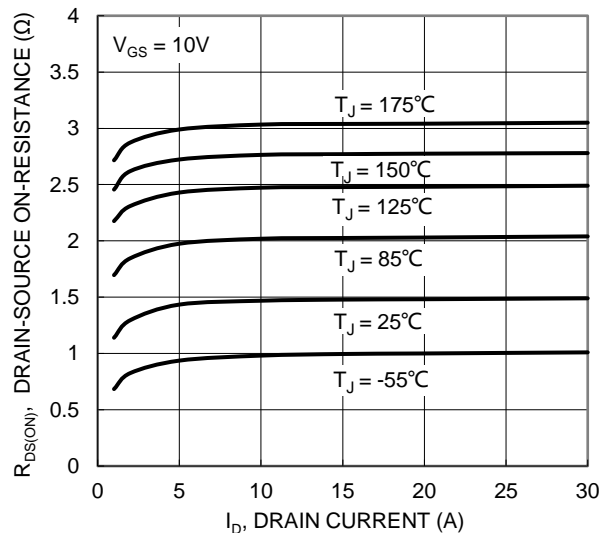


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

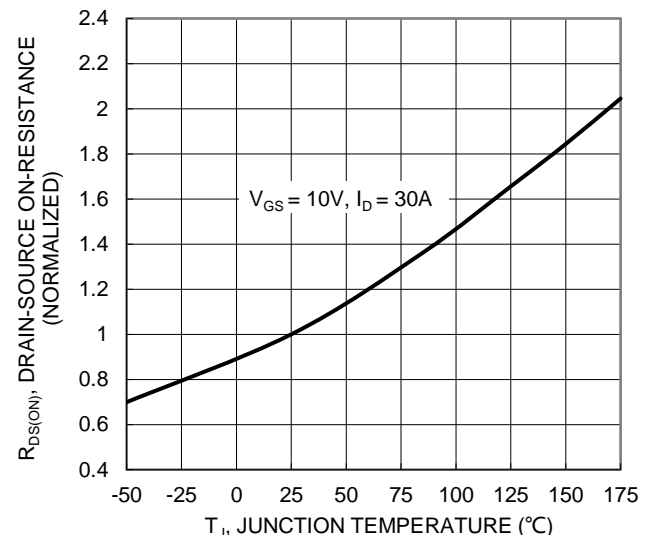
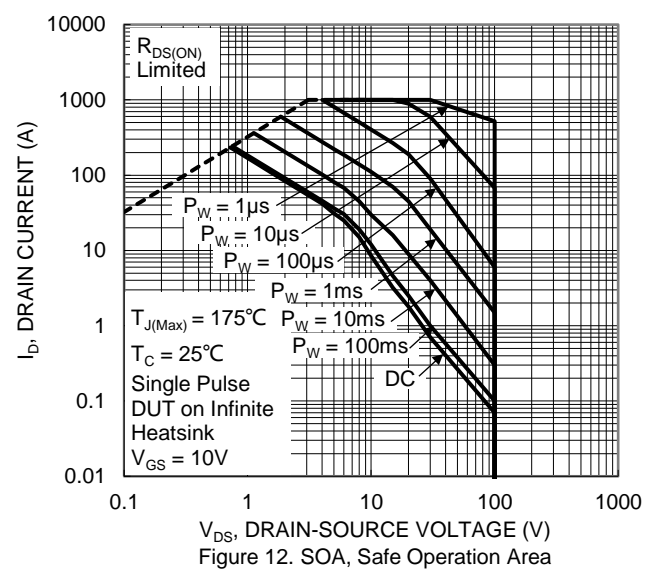
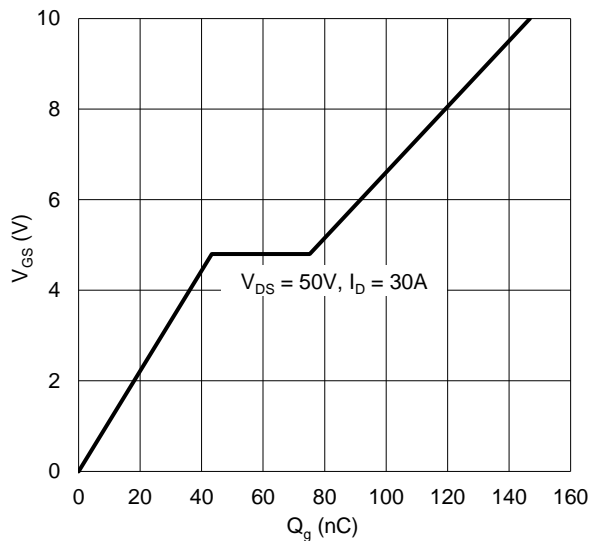
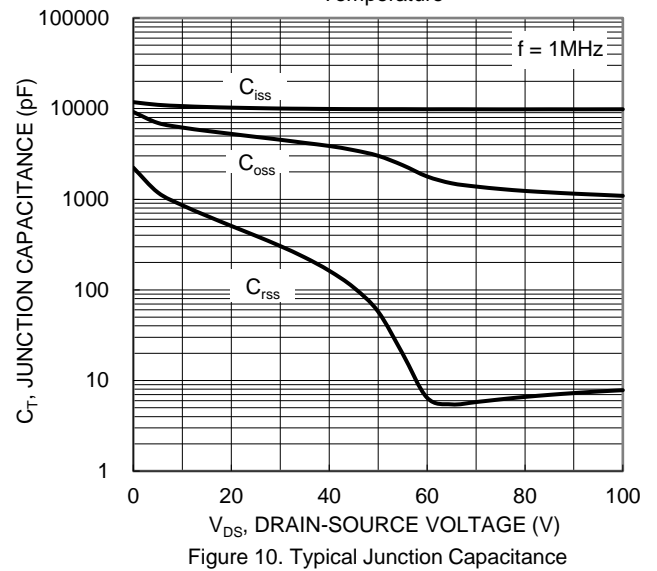
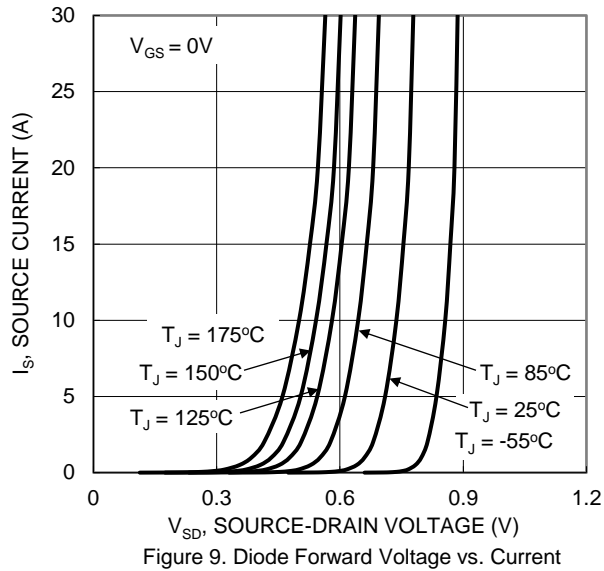
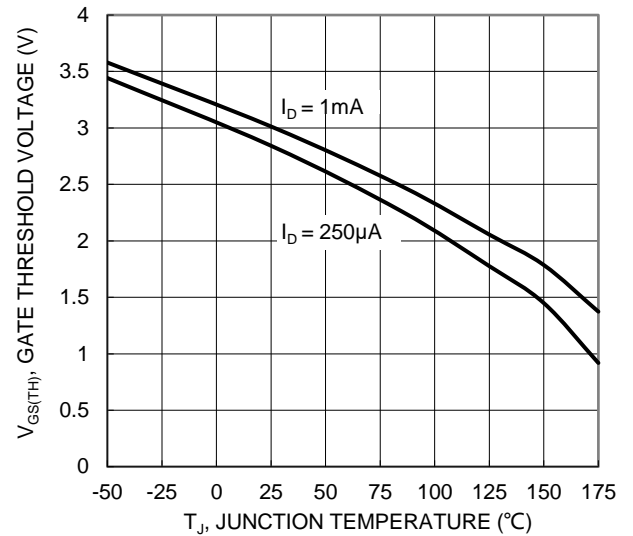
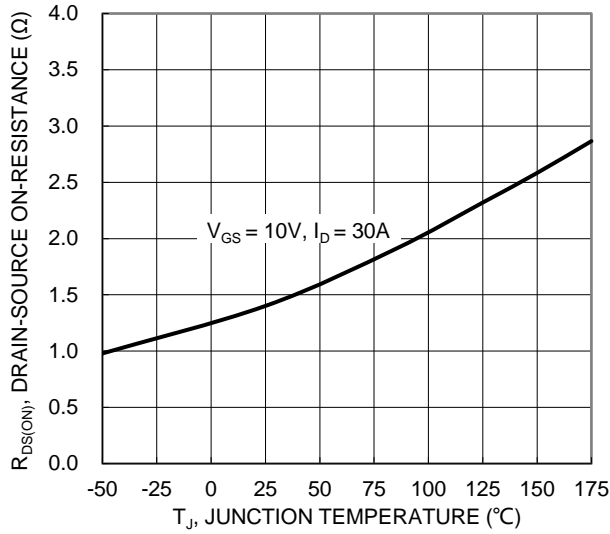


Figure 6. On-Resistance Variation with Temperature



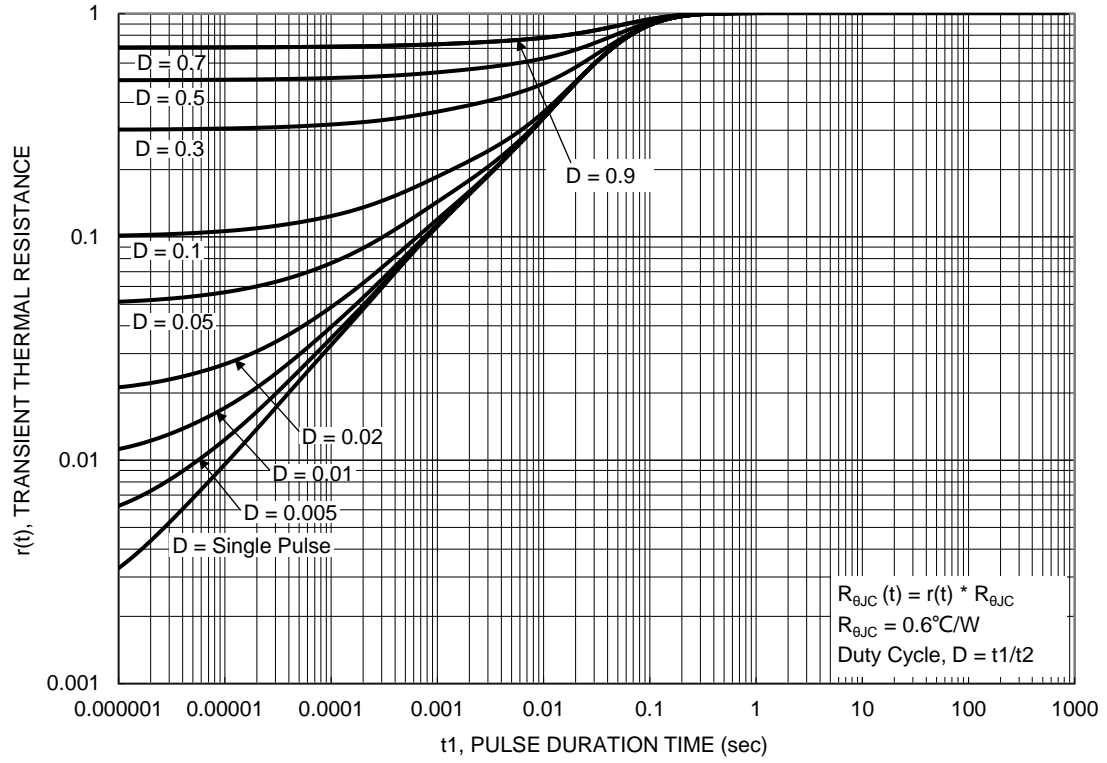
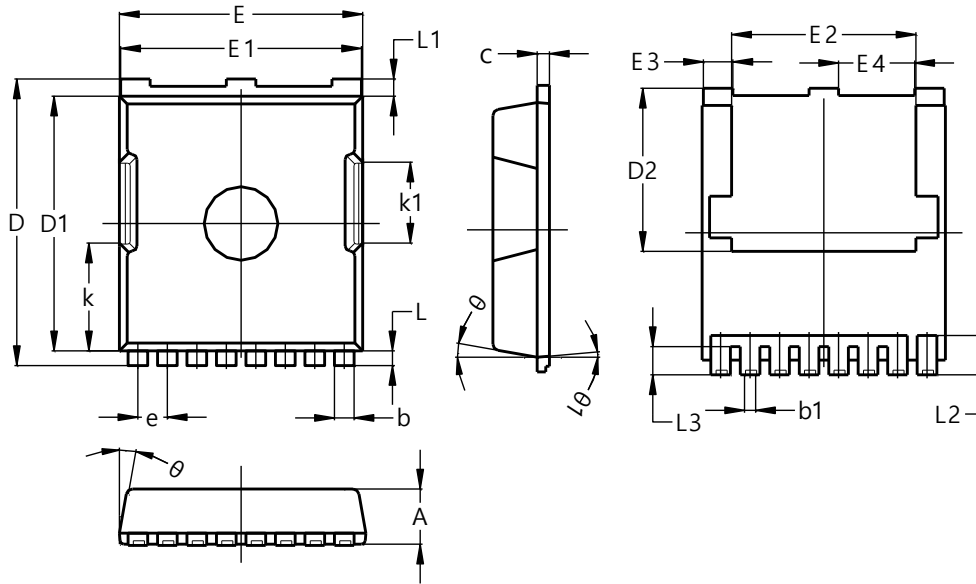


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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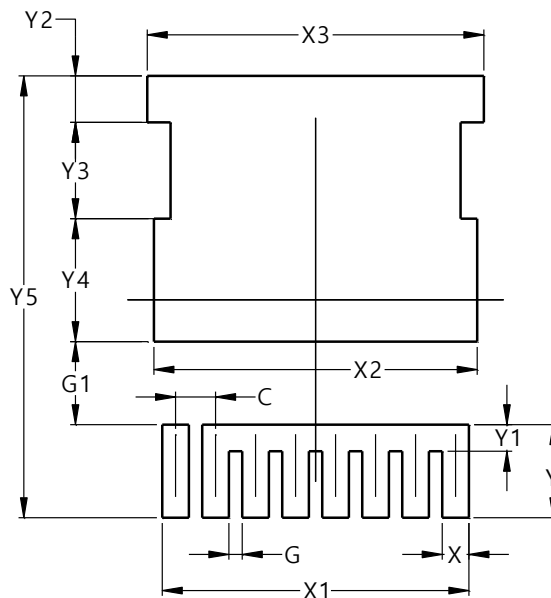


POWERDI1012-8			
Dim	Min	Max	Typ
A	2.20	2.40	2.30
b	0.70	0.90	0.80
b1	0.42	0.50	0.45
c	0.40	0.60	0.50
D	11.48	11.88	11.68
D1	10.23	10.53	10.38
D2	6.45	6.85	6.65
E	9.70	10.10	9.90
E1	9.70	9.90	9.80
E2	7.00	8.00	7.50
E3	1.10	1.30	1.20
E4	3.00	3.20	3.10
e	1.20 BSC		
k	4.39 REF		
k1	3.30 REF		
L	0.50	0.70	0.60
L1	0.50	0.90	0.70
L2	1.40	1.80	1.60
L3	1.00	1.30	1.15
θ	0°	15°	10°
θ1	0°	10°	5°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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Dimensions	Value (in mm)
C	1.200
G	0.400
G1	2.500
X	0.800
X1	9.200
X2	9.700
X3	10.100
Y	2.800
Y1	0.800
Y2	1.400
Y3	2.900
Y4	3.700
Y5	13.300

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